



MALTA monolithic Pixel sensors in TowerJazz 180 nm technology

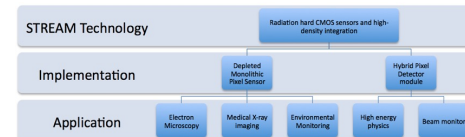


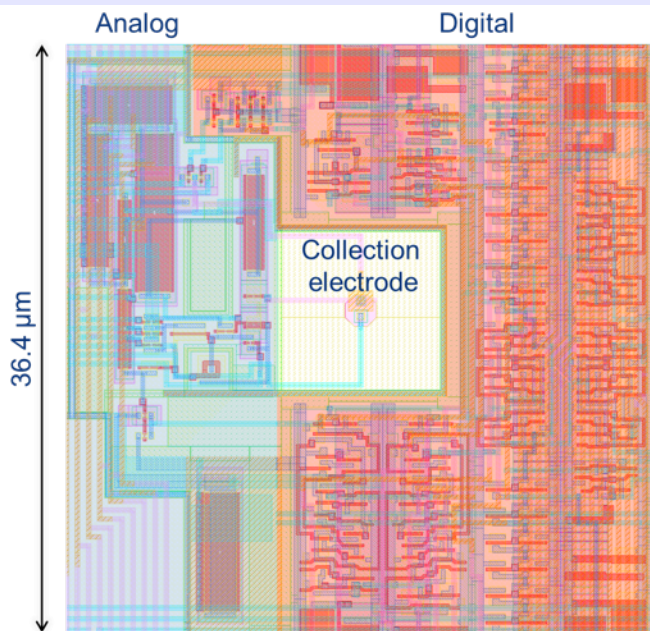
Carlos Solans
(CERN)



Philip Allport, Ignacio Asensi Tortajada, Vlad Berlea, Craig Buttar, Daniela Bortoletto, Valerio Dao, Roberto Cardella, Florian Dachs, Dominik Dobrijevic, Matt LeBlanc, Mateusz Dyndal, Leyre Flores Sanz de Acedo, Andrea Gabrielli, Abhishek Sharma, Heidi Sandaker, Heinz Pernegger, Petra Riedler, Milou van Rijnbach, Walter Snoeys, Tomislav Suligoj, Julian Weick, Steven Worm, Marlon Barbero, Pierre Barrillon, Patrick Breugnon, Pierre Pangaud, Yavuz Degerli, Amr Habib, Tomas Hemperek, Magdalena Munker, Kostas Moustakas, Philippe Schwemling, Tianyang Wang, Norbert Wermes

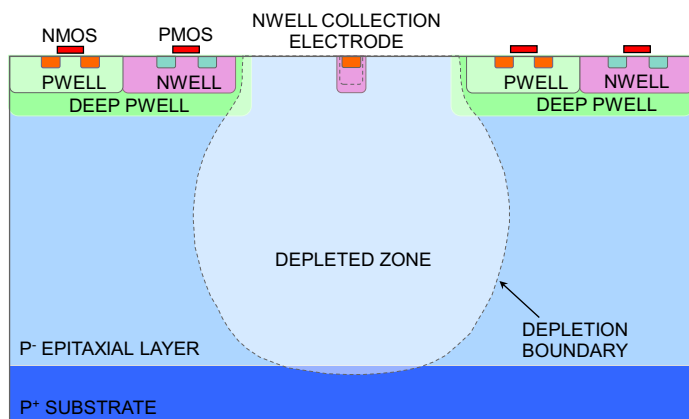
- Following the success from STREAM Innovative Training Network
- CERN EP R&D Programme on Technologies for future Experiments work packages 1.2 and 1.3 on Monolithic Pixel detectors
 - Innermost radii for maximum performance
 - Outer-layers as cost effective pixel trackers
 - High granularity and low material budget
 - Stitching and thinning of sensors
 - Module studies
- AIDA Work package 5 on Depleted Monolithic Active Pixel Sensors
 - Development of radiation hard DMAPS
 - Design and fabrication of test structures
 - Development of readout systems
 - Characterization of devices



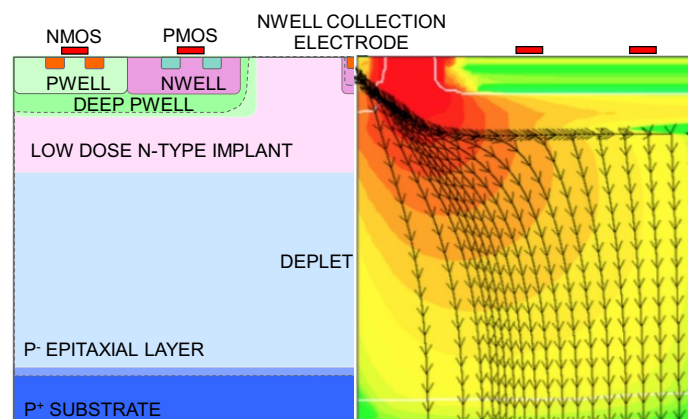


- Pixel size $36.4 \times 36.4 \mu\text{m}^2$ allows good spatial resolution
- 2-3 μm collection electrode provides minimal capacitance ($< 5\text{fF}$)
- 3.4 - 4 μm spacing to electronics avoids cross-talk
- Asynchronous read-out without clock distributed to the cell
- 1 μW/pixel to minimize power consumption

- High resistivity Epitaxial process 25 or 30 μm thick
- Reach full depletion around $\sim 10\text{ V}$
- High signal to noise ratio ~ 20
 - Expected MIP energy deposition (1500 e-) and low noise
- Modified “standard” process
 - Additional low dose n- layer to improve depletion under the deep p-well
 - Radiation tolerance had to be evaluated

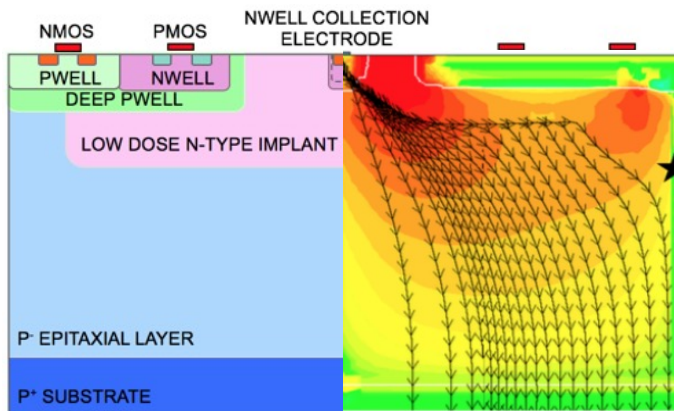
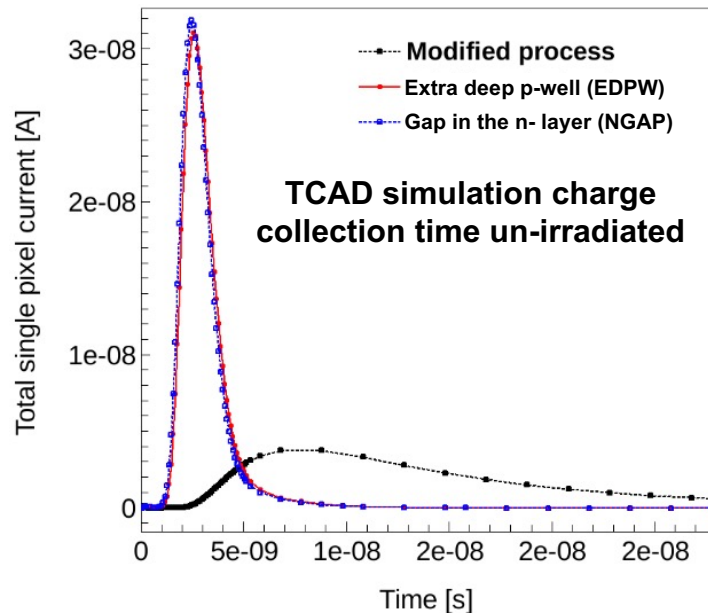


TowerJazz process (ALPIDE)

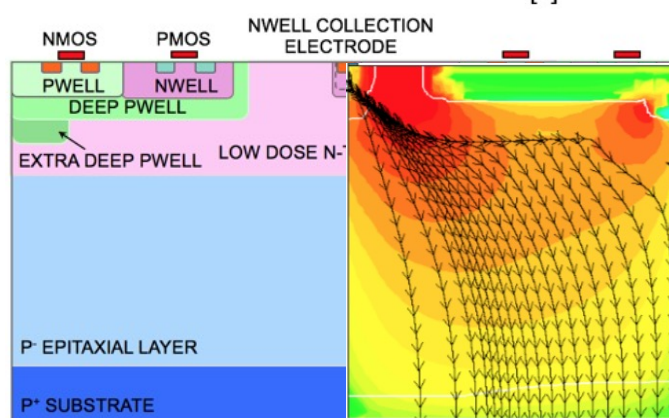


Standard modified process

- Process modified based on TCAD simulations
 - Increase the lateral field configuration
 - Reduce charge collection time
- Gap in the n-layer
 - 4 μm gap in the low dose n-layer
- Extra-deep p-well
 - 5 μm wide additional p-well implant

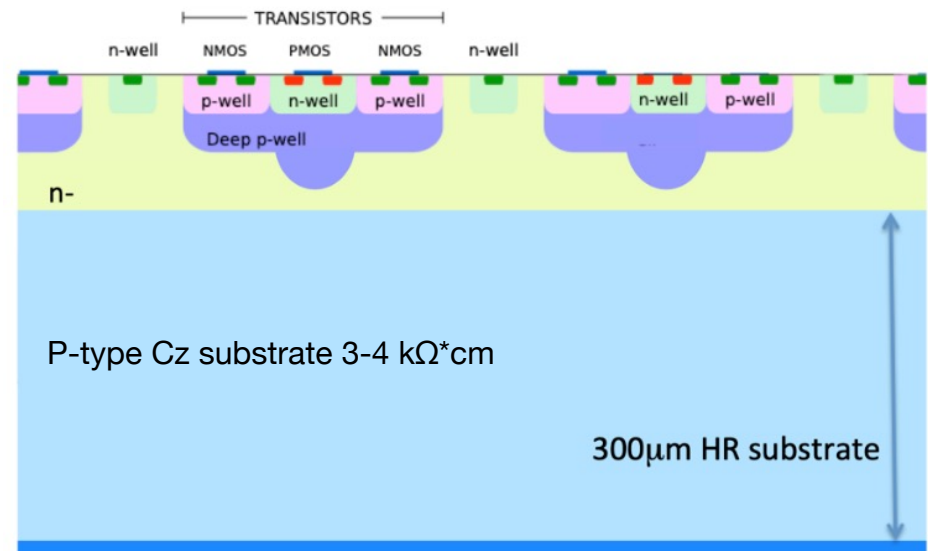
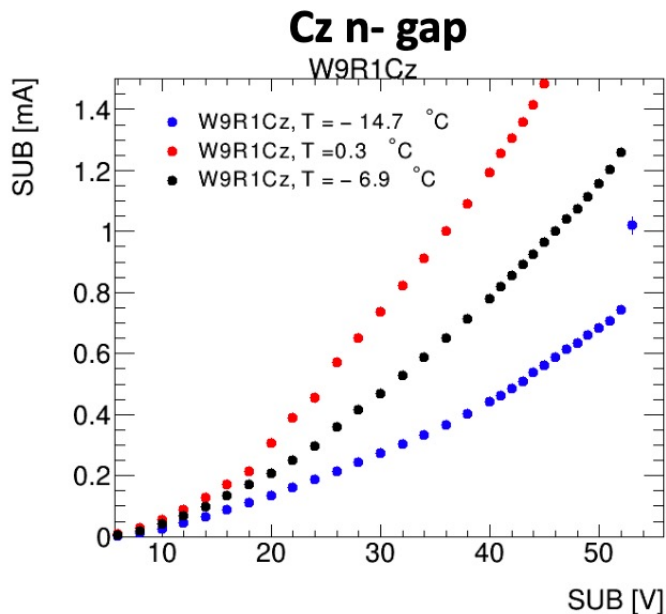


Gap in the n-layer (n-gap)

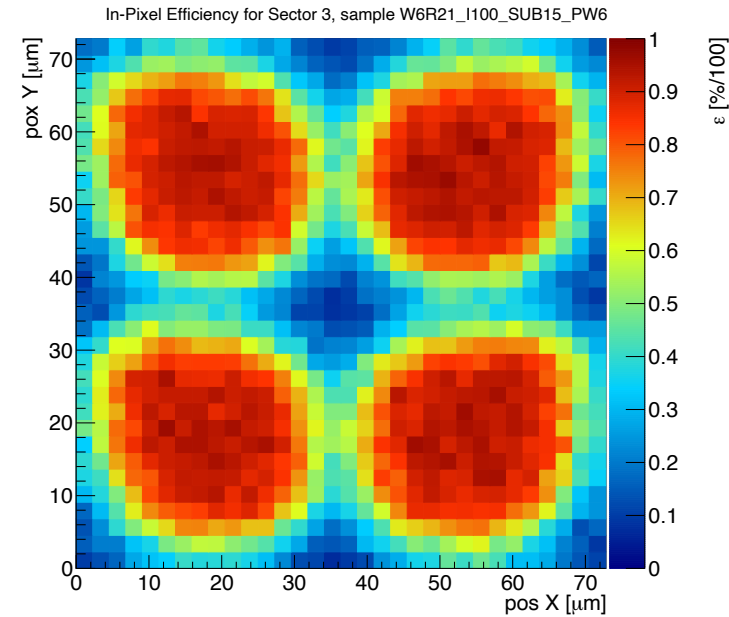
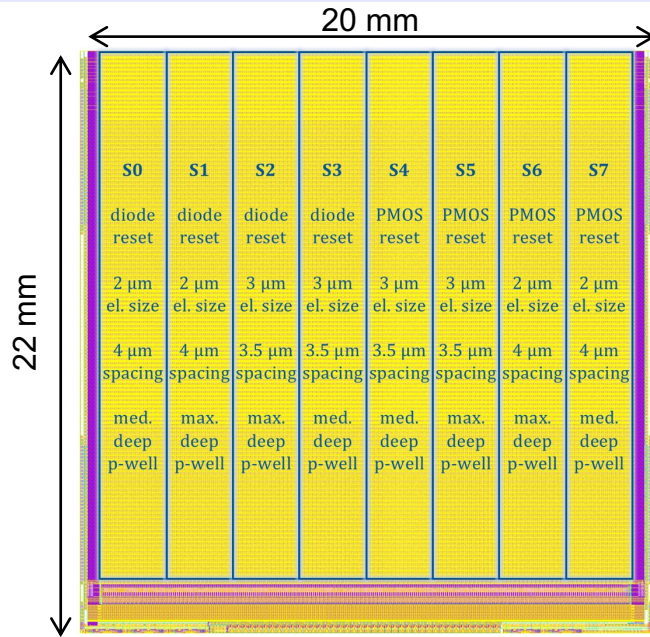


Extra deep p-well (EDPW)

- Possibility of processing on high resistivity Czochralski substrate
 - Resistivity of $\sim 3\text{-}4 \text{ k}\Omega\cdot\text{cm}$
 - Can operate at 50V reverse bias for larger depletion
 - Increased charge collection
 - Aim for better time resolution and higher radiation hardness
- Implement the same process modifications
 - Continuous n-layer (standard), gap in the n-layer (n-gap), extra deep p-well

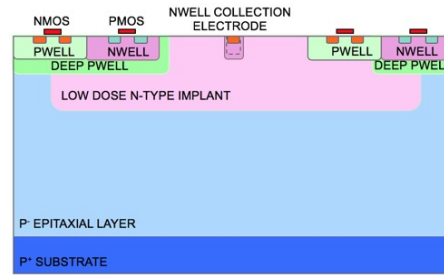
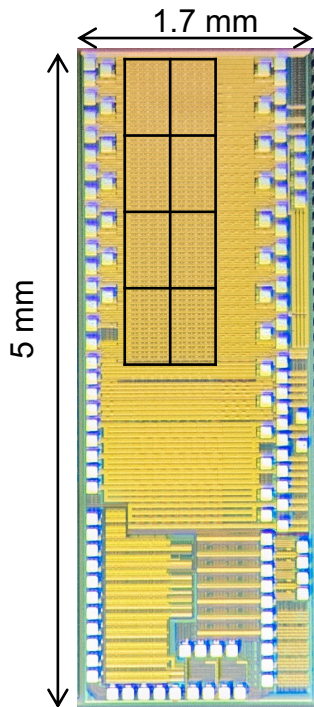


[H. Pernegger, NIM A 986 \(2021\) 164381](#)

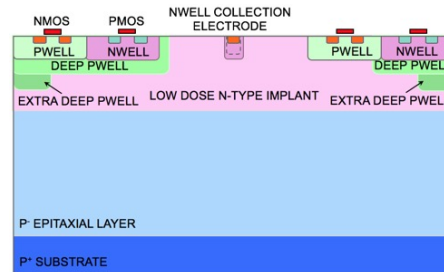


Sector 3 efficiency projected to a 2x2 pixel array of sample irradiated to 10^{14} $n_{\text{eq}}/\text{cm}^2$

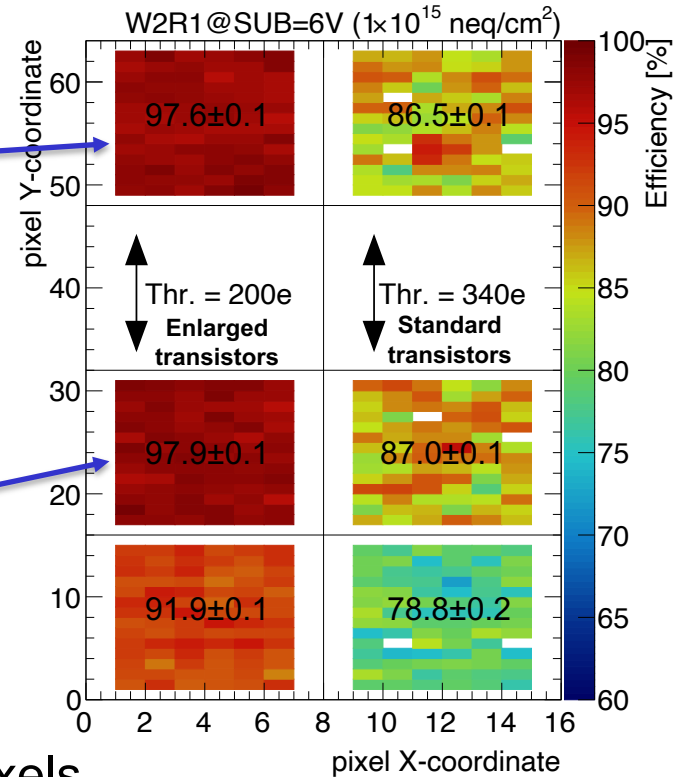
- 22 x 20 mm² full size demonstrator
- 512 x 512 pixels (>250k) grouped in 8 sectors
- Fully clock-less matrix architecture with 37-bit bus read-out
- 10 mW/cm² digital + 70 mW/cm² analog power
- Efficiency degraded at pixel edges after 10^{14} $n_{\text{eq}}/\text{cm}^2$



Gap in the n-layer

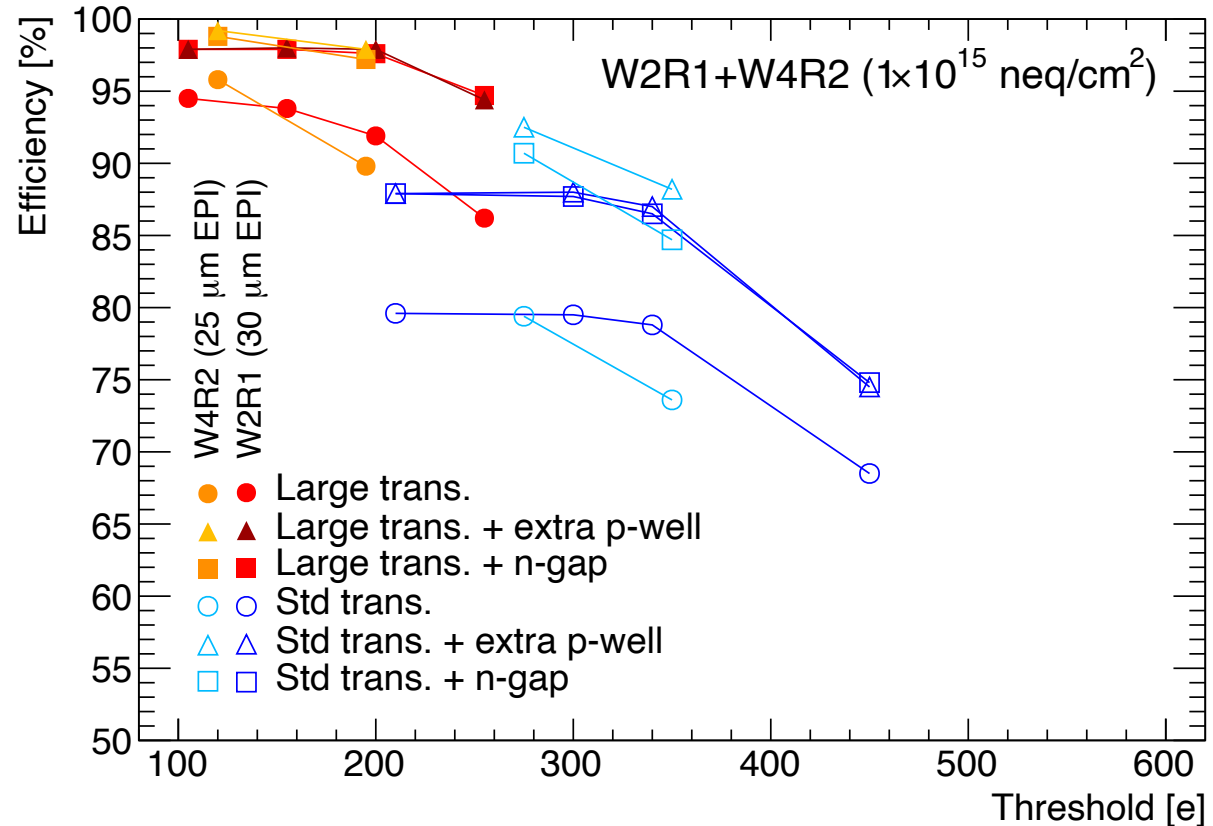


Extra deep p-well

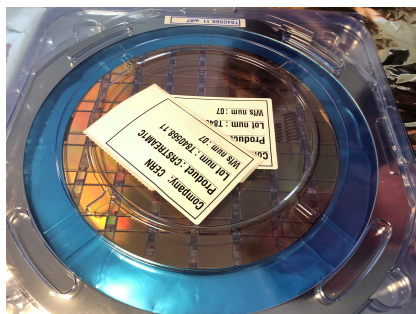
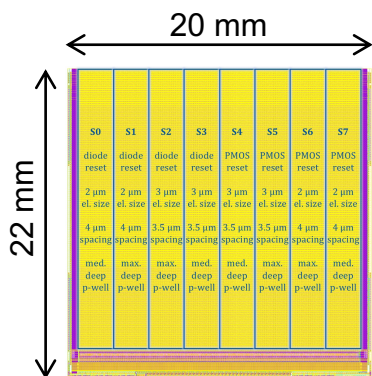


- 5 x 1.7 mm² demonstrator with 64 x 16 MALTA pixels
- 4 different process modifications to address radiation hardness
- 2 capacitor sizes to address RTS noise
- On chip data synchronization using a custom RAM memory
- Modified processes with enlarged transistors radiation hard to 10^{15} n_{eq}/cm²

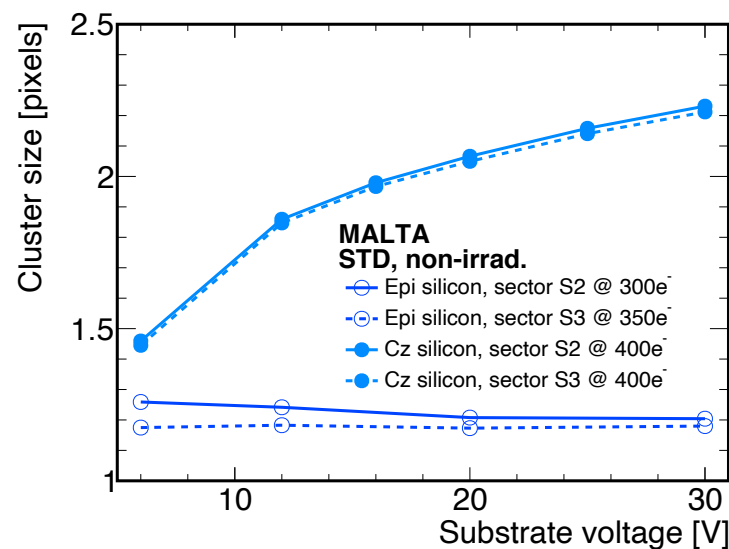
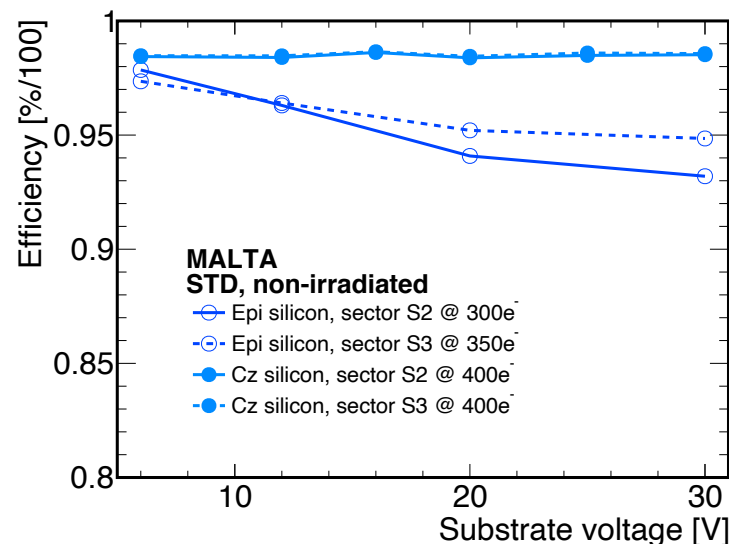
- Two trends: standard size and enlarged size transistors
- Enlarged transistors reach lower thresholds (~ 150 e⁻) and higher efficiency (>98%)
- Slightly higher efficiency for additional process modifications
- Similar performance between 25 μm and 30 μm EPI thickness

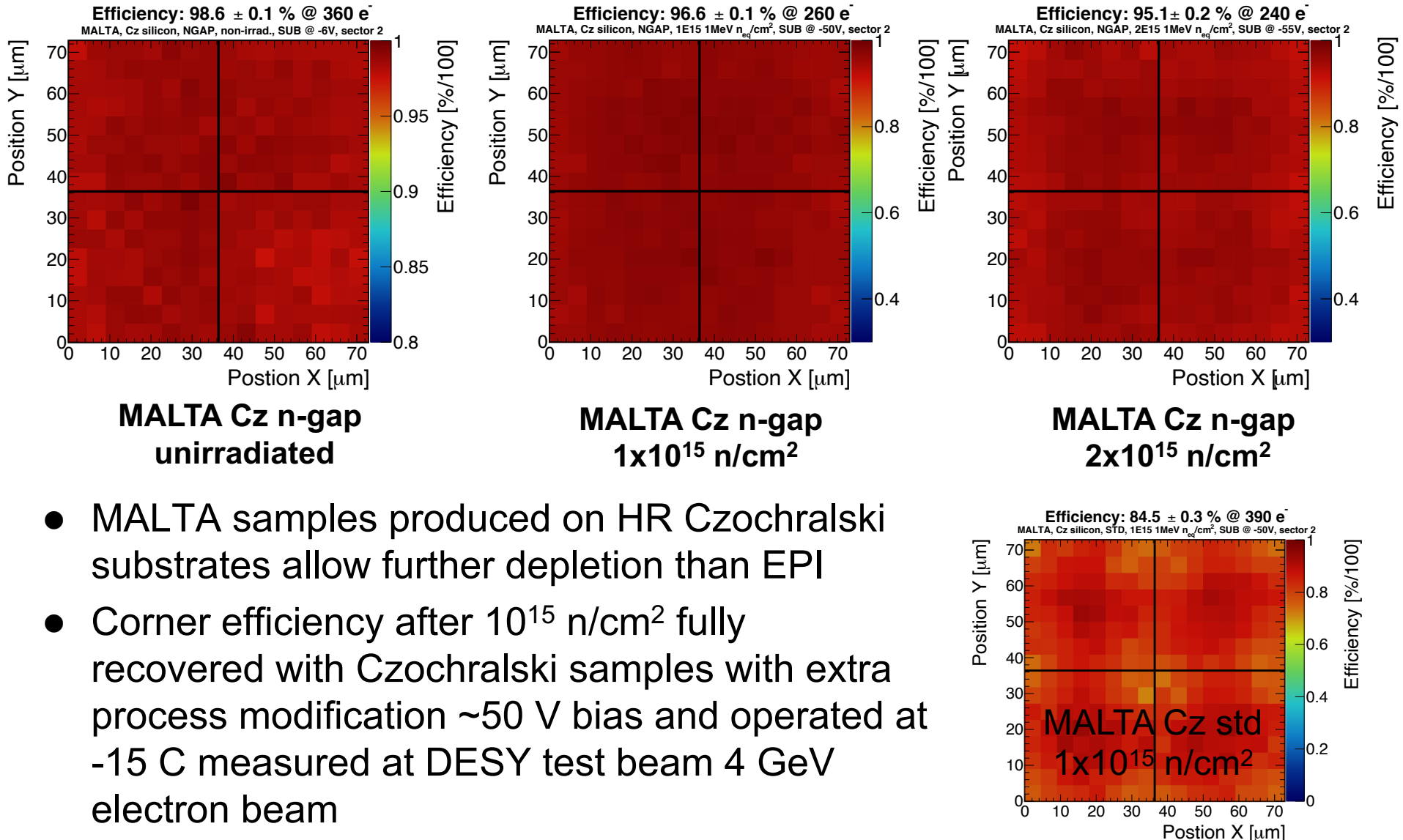


Efficiency versus threshold for two different Mini-MALTA samples 30 μm EPI and 25 μm EPI neutron irradiated to 10^{15} n/cm², and measured with 3 GeV electron beam at ELSA, with 6 V bias voltage

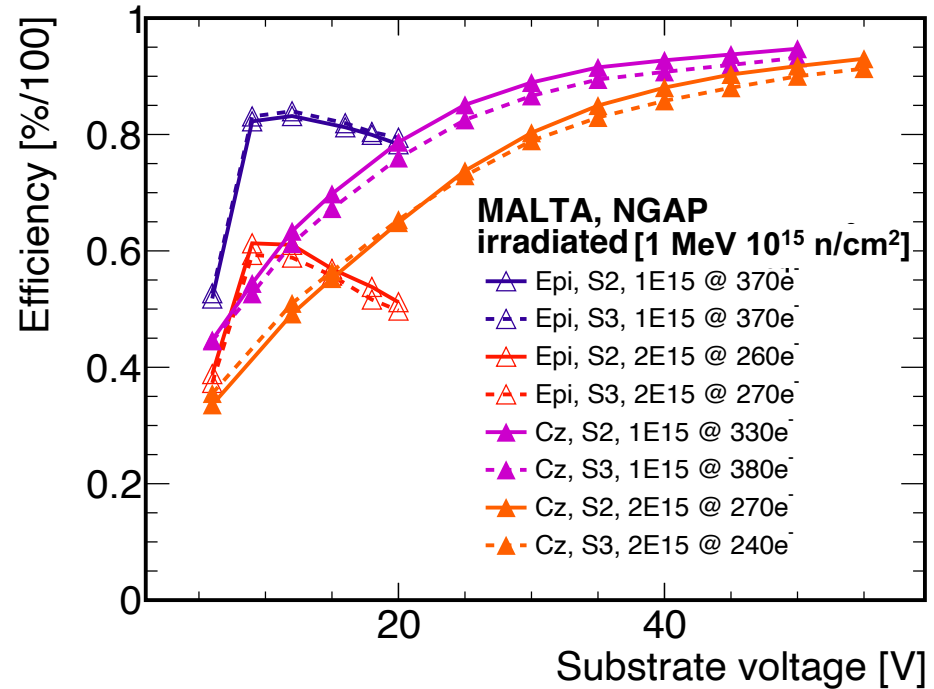
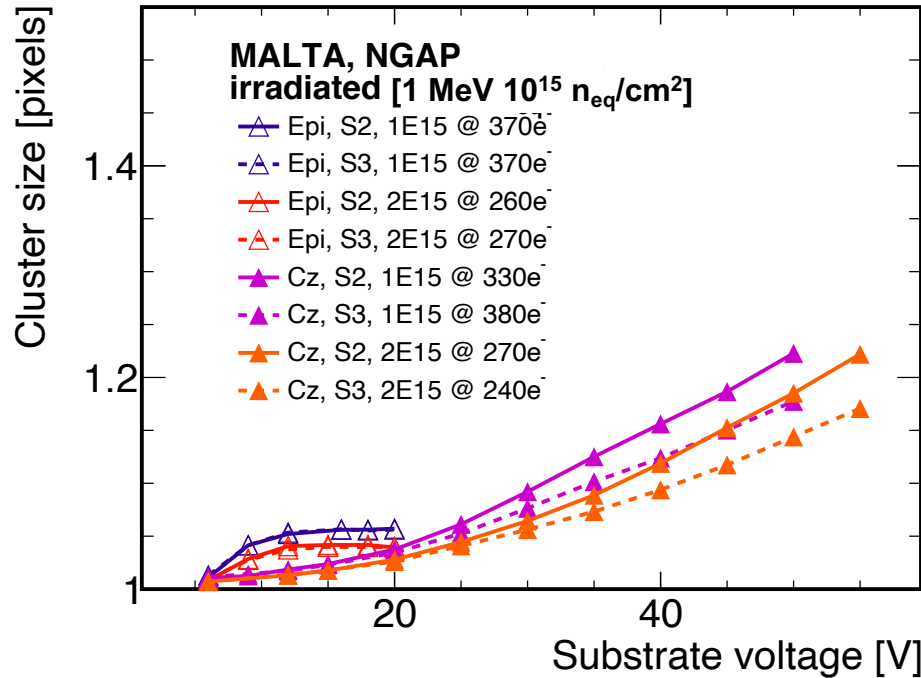


- 22 x 20 mm² full size demonstrator with slow control improvements manufactured on Epitaxial and Czochralski substrates
- Efficiency of Epitaxial samples decreases with bias voltage as opposed to Czochralski sensors
- Cluster size on Czochralski samples reaches 2.2 at 30V as opposed to Epi

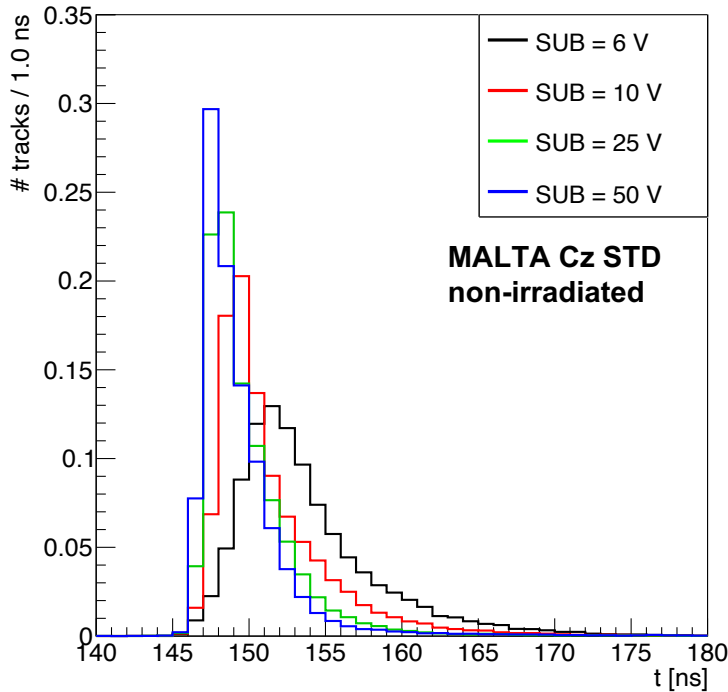




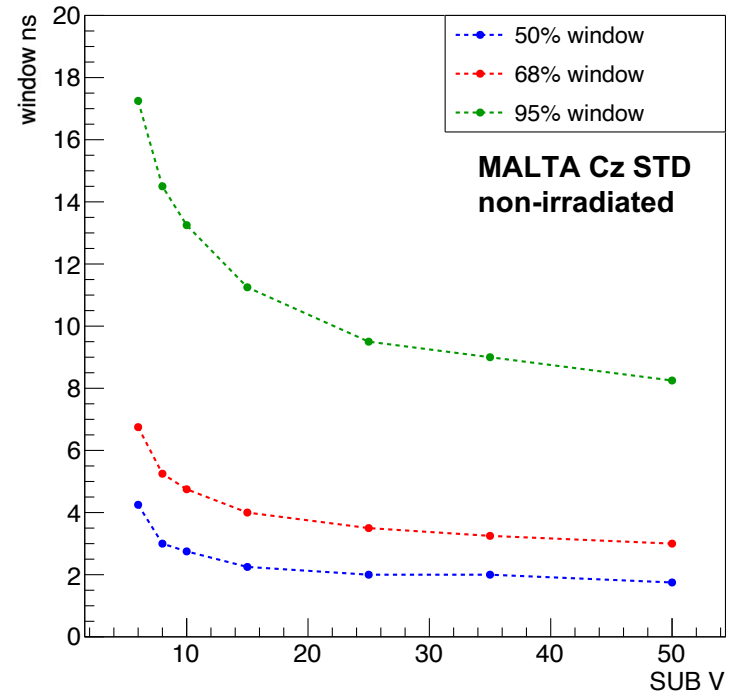
- MALTA samples produced on HR Czochralski substrates allow further depletion than EPI
- Corner efficiency after $10^{15} n/cm^2$ fully recovered with Czochralski samples with extra process modification ~ 50 V bias and operated at -15 C measured at DESY test beam 4 GeV electron beam



- MALTA epitaxial sensors irradiated at 10^{15} n/cm²
 - Cluster size remains at ~1.05 and reach maximum efficiency at ~12 V
- MALTA Czochralski sensors irradiated at 10^{15} n/cm²
 - Cluster size reaches ~1.2 at ~50V and reach full efficiency (>95%) at ~50 V

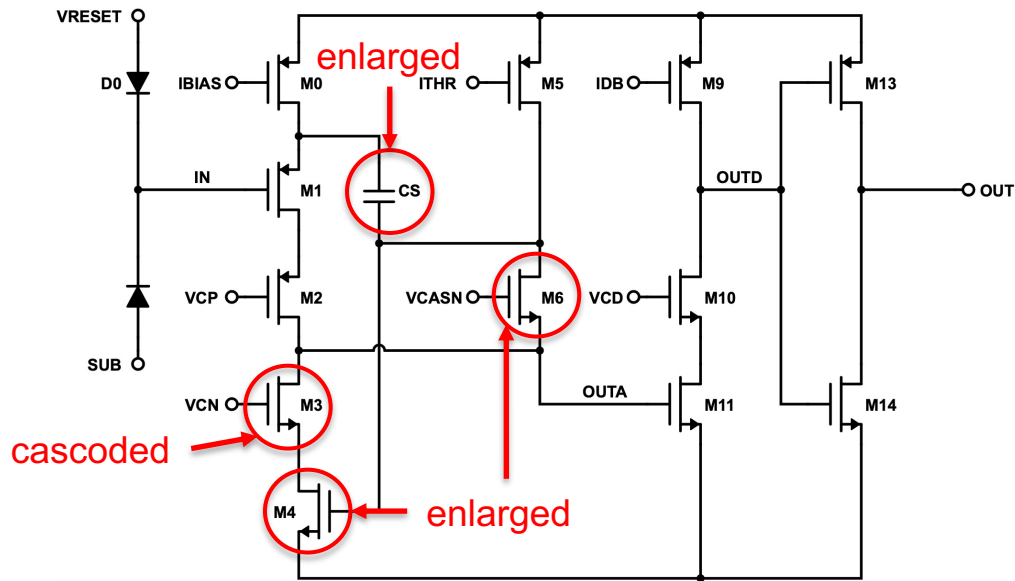


Time difference between MALTA hit and trigger signal at different substrate bias voltages

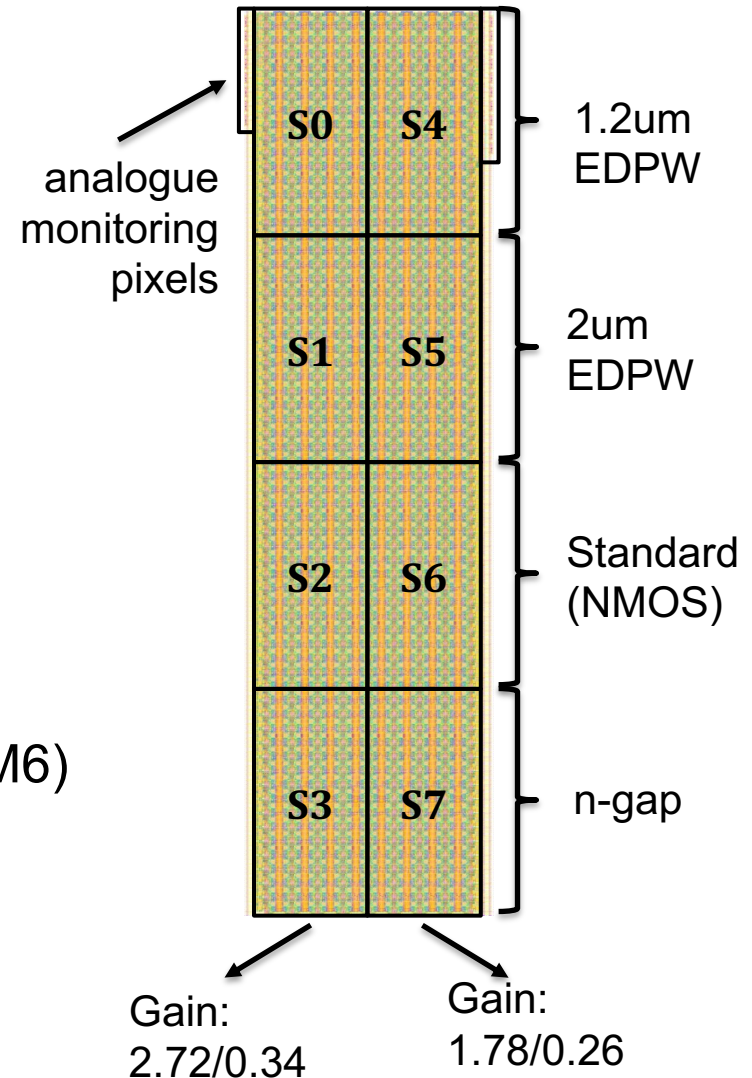


Integral curves of time difference distributions between MALTA hit and trigger signal

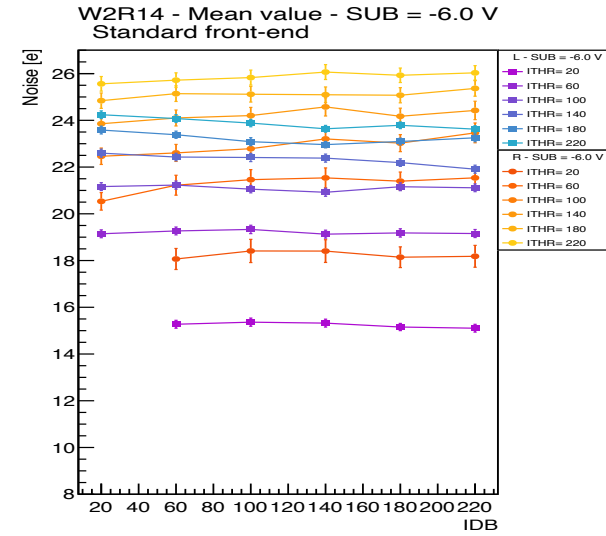
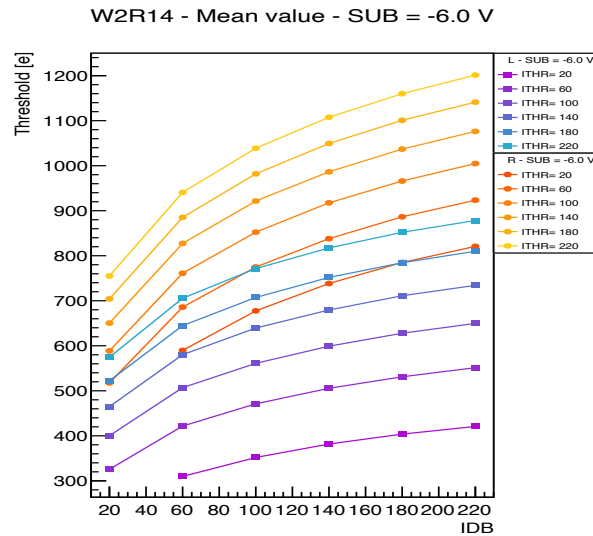
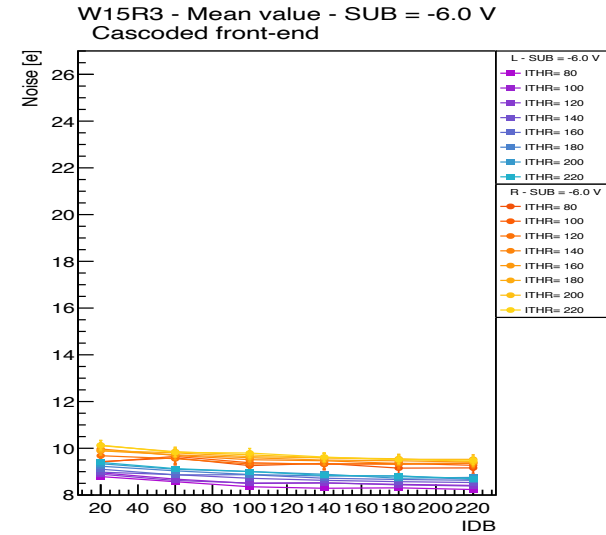
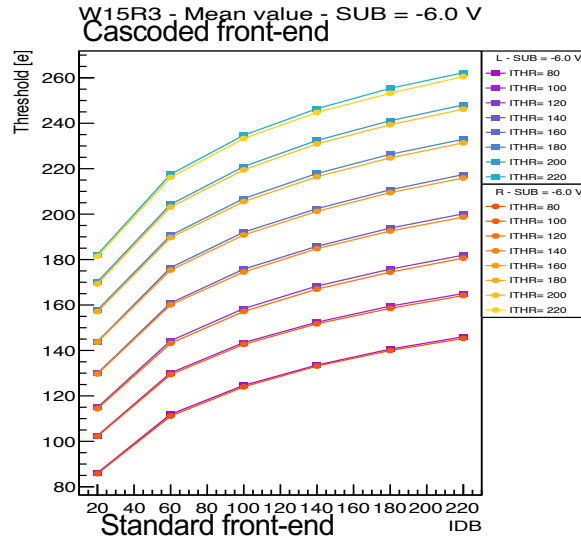
- Faster signal and higher amplitude at large substrate voltages reduce time-walk and narrow the time-difference distribution between trigger scintillator and non-irradiated MALTA Cz STD sample (measured with Pico-TDC*)
- 50% of the hits arrive within 2 ns at a substrate voltage above 15V

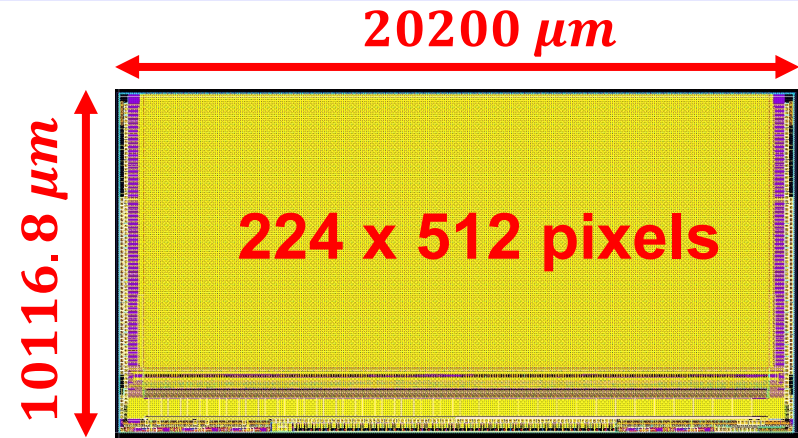
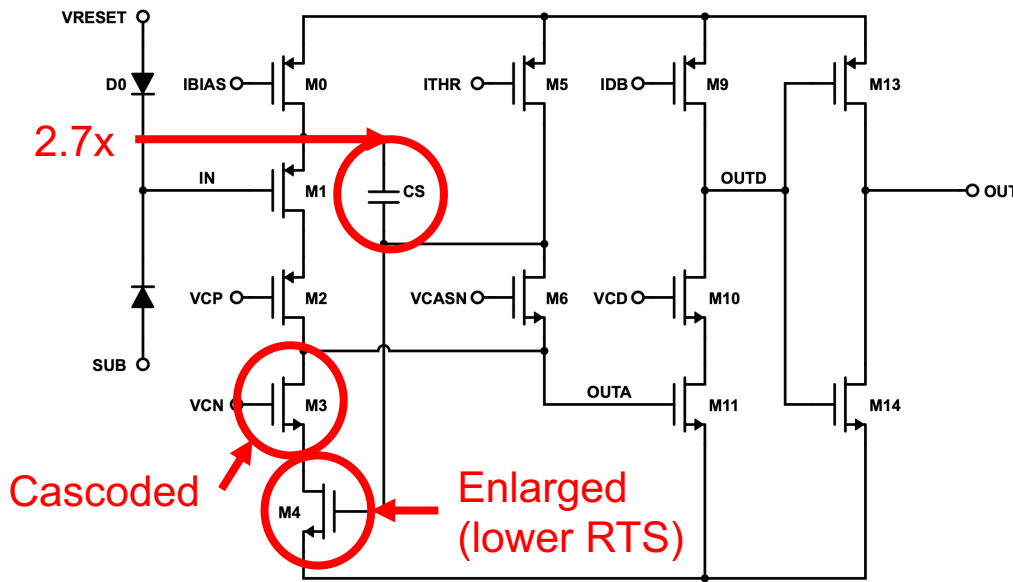


- All sectors have cascoed front-end (M3)
- Sectors 0 to 3 have higher gain (CS, M4, M6)
- Sectors 0 and 4 are 1.2 μm EPDW
- Sectors 1 and 5 are 2 μm EPDW
- Sectors 2 and 6 are standard n- layer
- Sectors 3 and 7 are n-gap



- Cascoded front-end implemented in Mini-MALTA split 7
- Reaches lower threshold values
- Threshold is less affected by the size of the other transistors
- Cascoded front-end has smaller noise
- Selected for the front-end of MALTA2

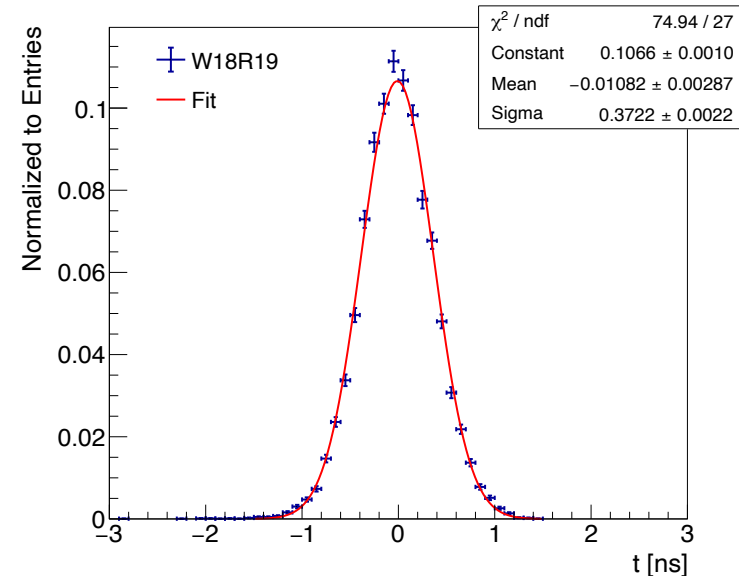


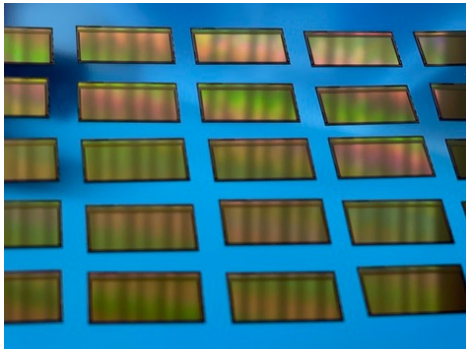


MALTA 2 foot-print

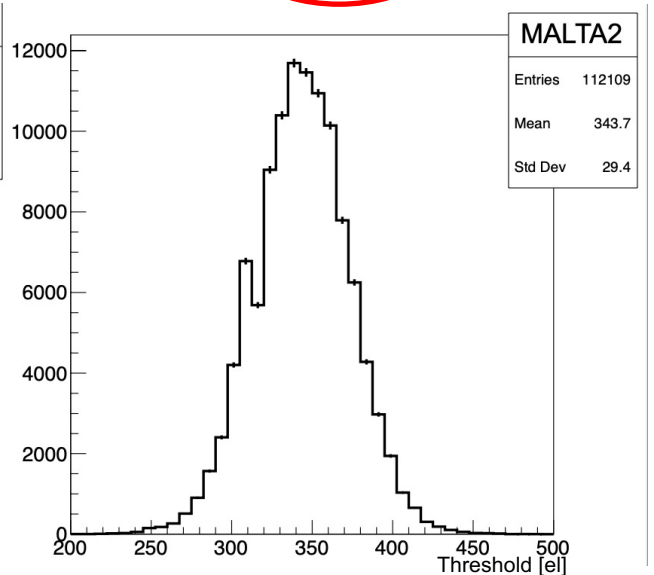
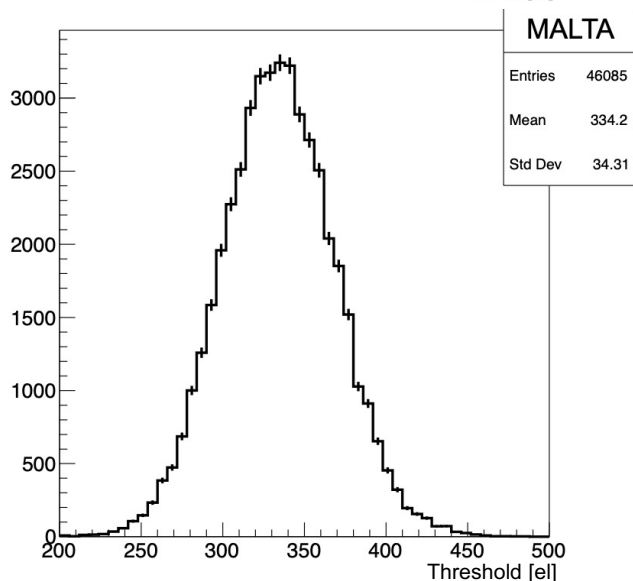
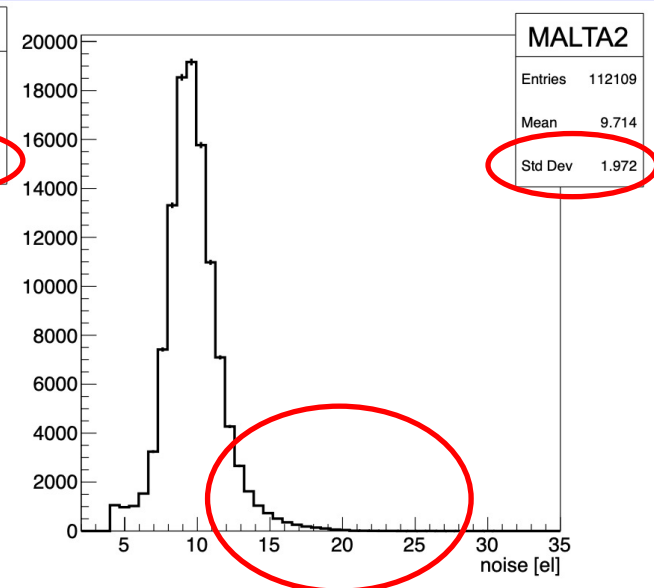
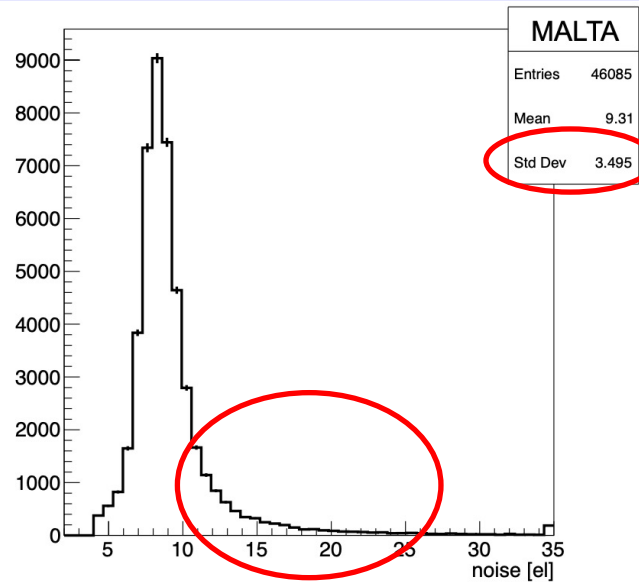
- 20 x 10 mm² size demonstrator
- 224 x 512 MALTA pixels
- Single pixel design
 - 2 μm col. el. size and 4 μm spacing
- Cascoded front-end from Mini-MALTA split 7
- Enlarged M4 transistor and CS capacitor
- Improved jitter in time propagation down the column

MALTA2 Cz XDP Very High Doped 100 μm

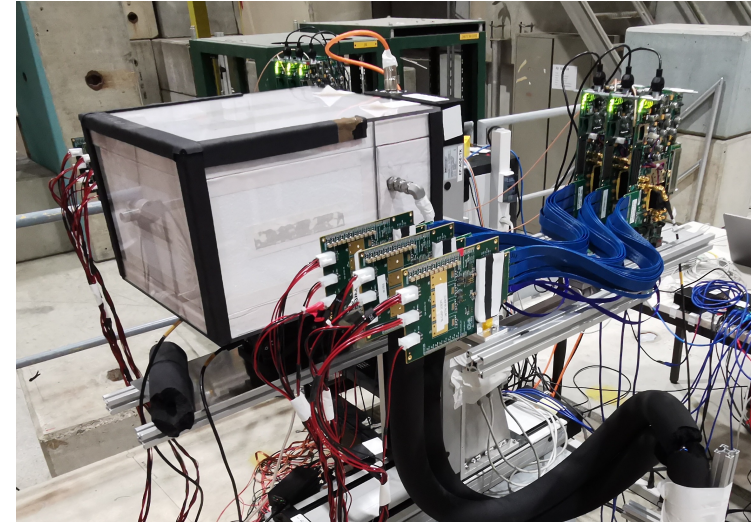




- MALTA2 has less RTS noise (reduced noise tails) compared to MALTA at the same threshold (~ 350 e-) and 6V bias
- Threshold dispersion similar to MALTA ($\sim 10\%$ of the mean)



- Custom MALTA telescope with fast read-out, online monitoring, and cold box for or irradiated samples
 - Up to 7 planes + DUT
 - or 6 planes + 2 DUT
- Triggering directly out of MALTA planes through combination of reference signals
 - Scintillator for better time reference
- Interface with pico-TDC for precise characterization of the timing properties of the signal
- Define ROI on tracking planes and check hits on DUT
- Confirmed results with MIMOSA telescope at DESY



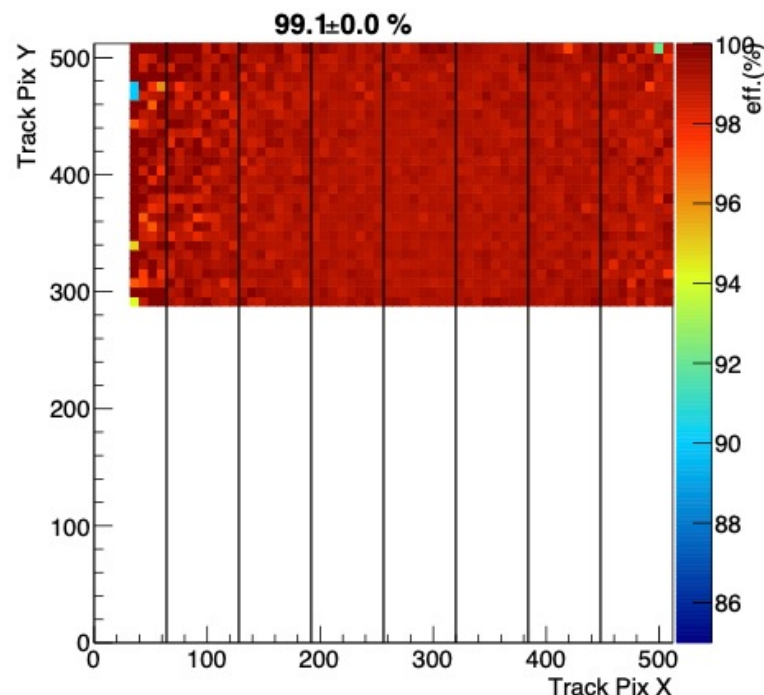
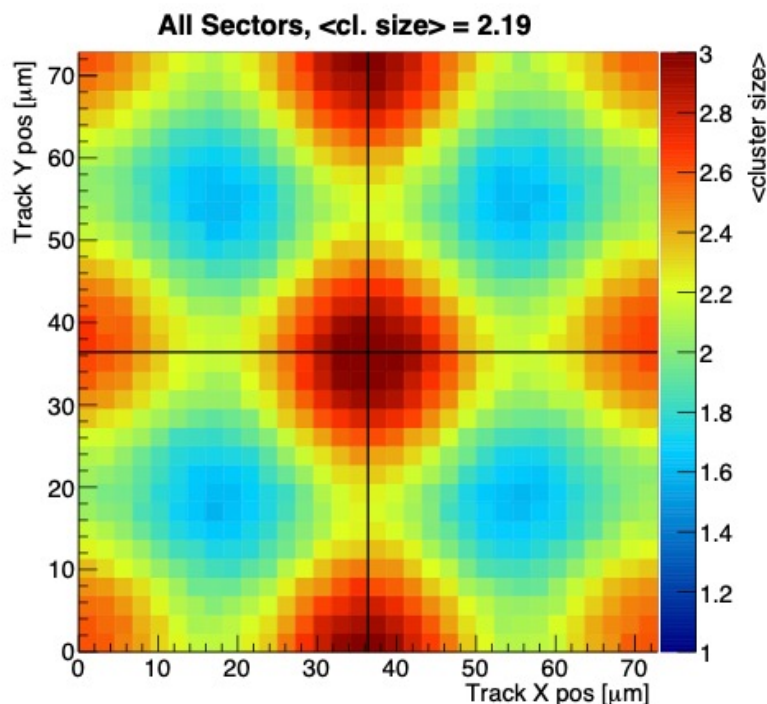
MALTA telescope at SPS



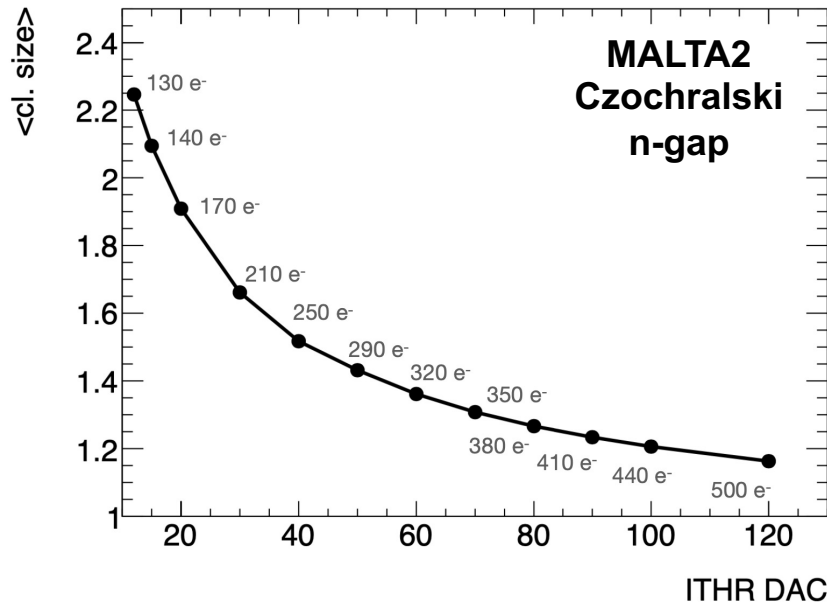
Detail of MALTA and MALTA2 planes

MALTA Cz std -50V unirradiated

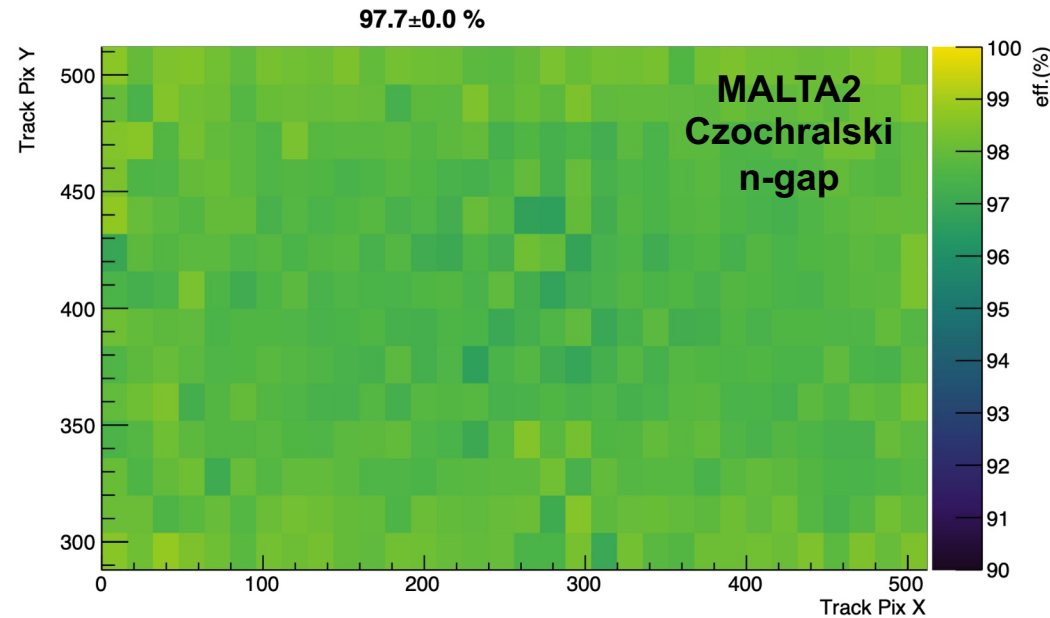
MALTA2 -6V unirradiated



- Ongoing test-beam campaign at SPS from July to November
- Test radiation hardness of MALTA2 above 10^{15} n/cm²
- Large cluster size from MALTA Cz standard at the pixel corners
- Full efficiency for un-irradiated MALTA2 EPI sensors at -6V



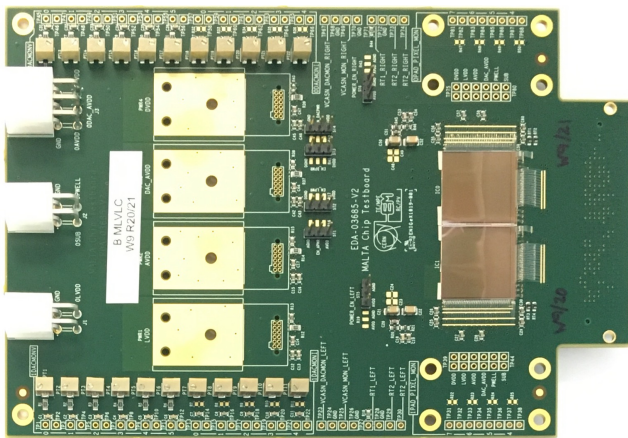
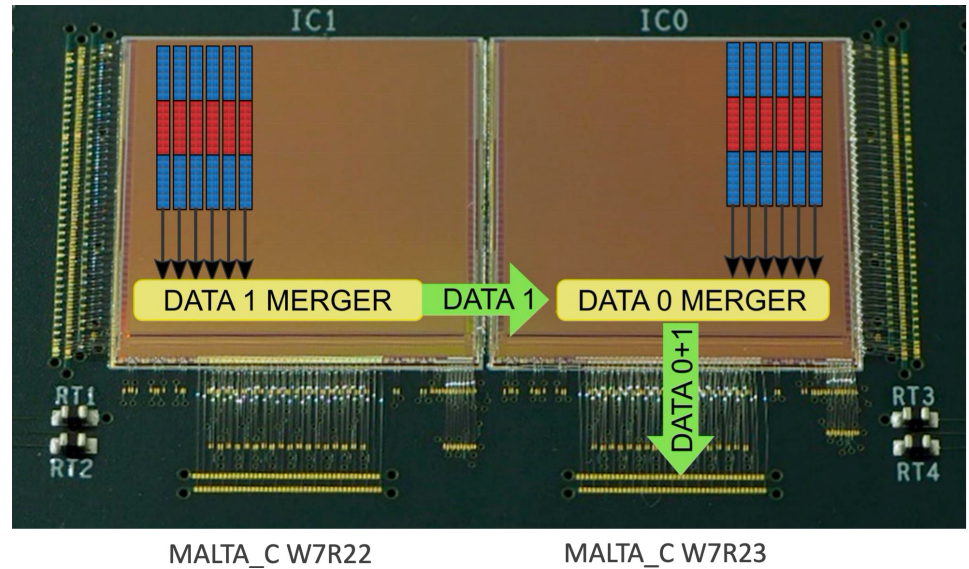
Average cluster size of versus ITHR at fixed IDB 120.
For every data point the corresponding threshold is quoted.



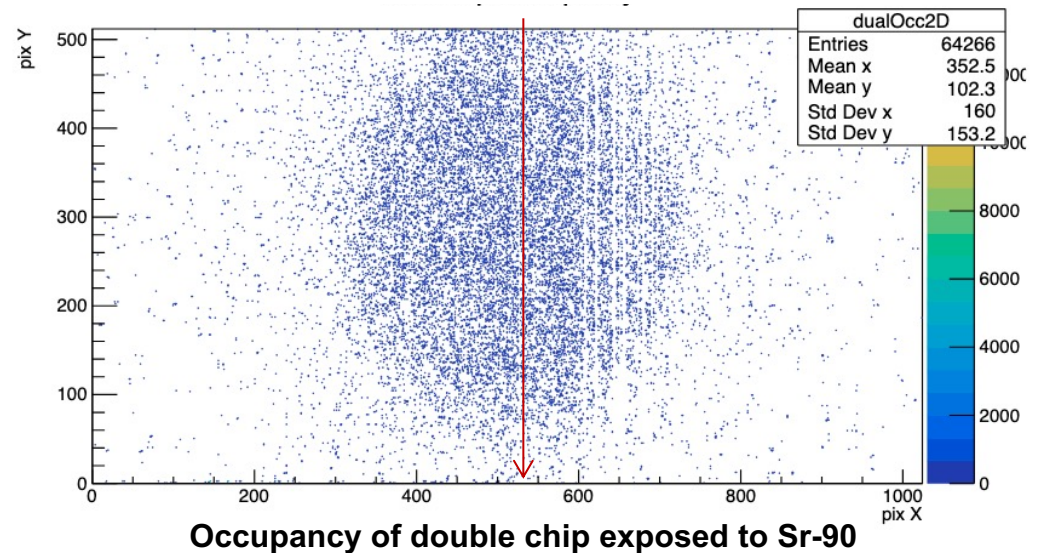
Efficiency map of un-irradiated MALTA 2 Cz n-gap
at 320 electrons threshold and 6 V bias

- Full efficiency for un-irradiated MALTA2 Cz n-gap sensors at -6V
- Cluster size reaches 2.2 at 130 electron threshold and -6V bias

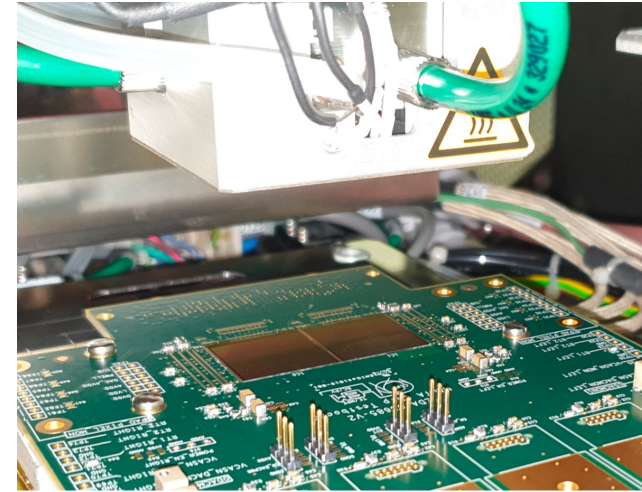
- Data from MALTA can be routed to another MALTA to the left or to the right through CMOS outputs
- Aim to target larger sensing surfaces and reduce services



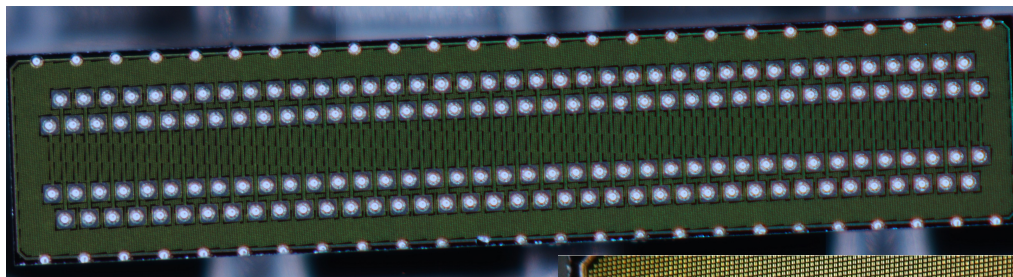
Dual chip carrier board



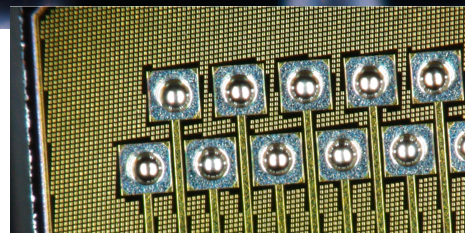
- Silicon bridge can connect two MALTA samples with 10 μm positioning precision
- Bridge is attached to chips with ACF glue, 1 kg of pressure and at 150°C for 10 seconds



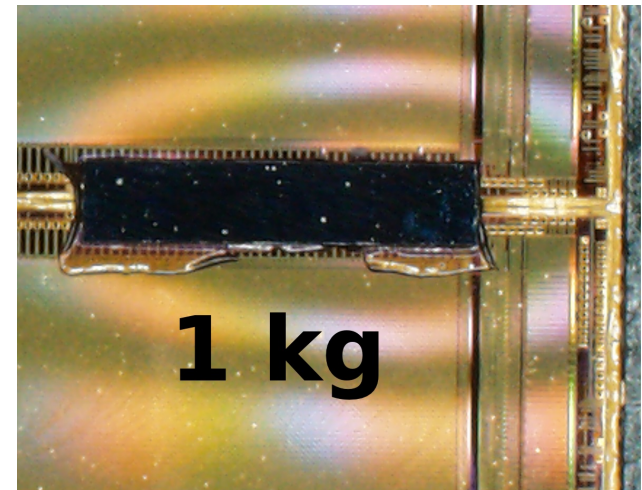
Positioned MALTA 2 chip carrier



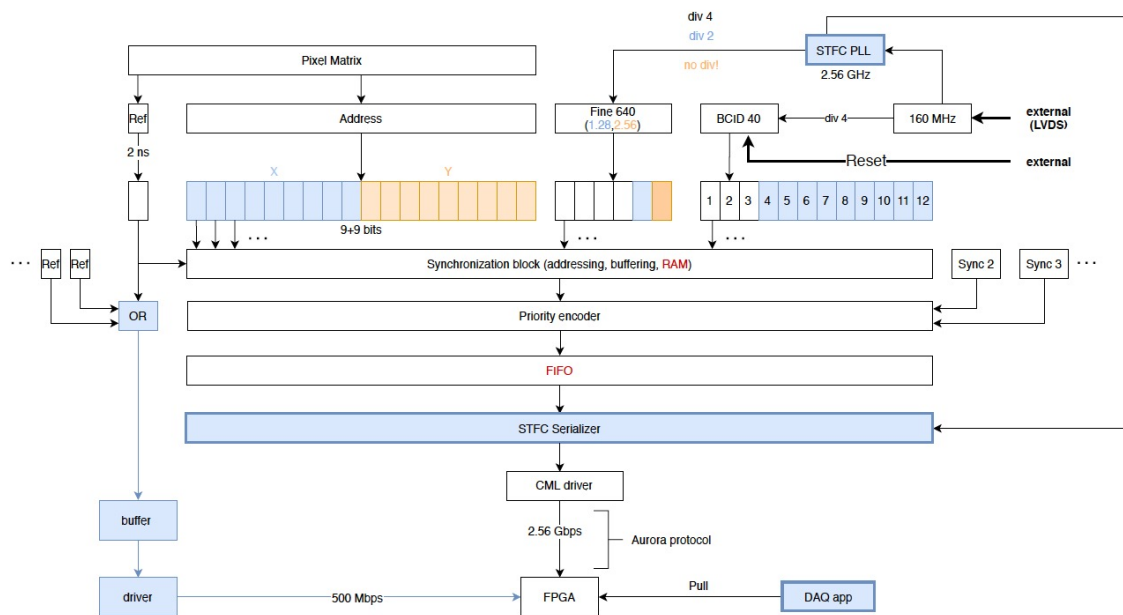
Silicon bridge



Tin studs on silicon bridge

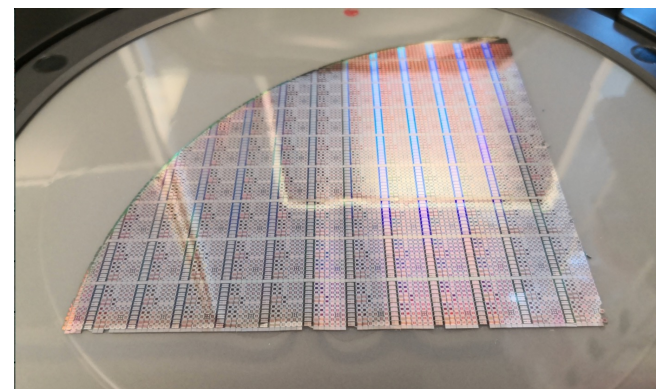
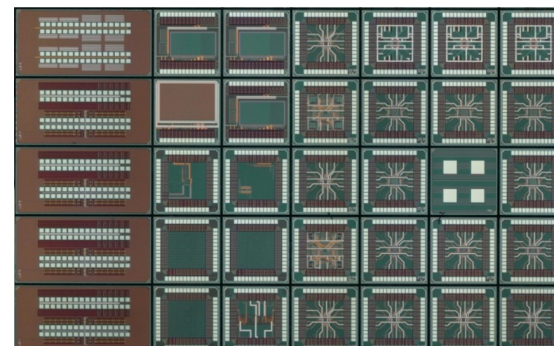
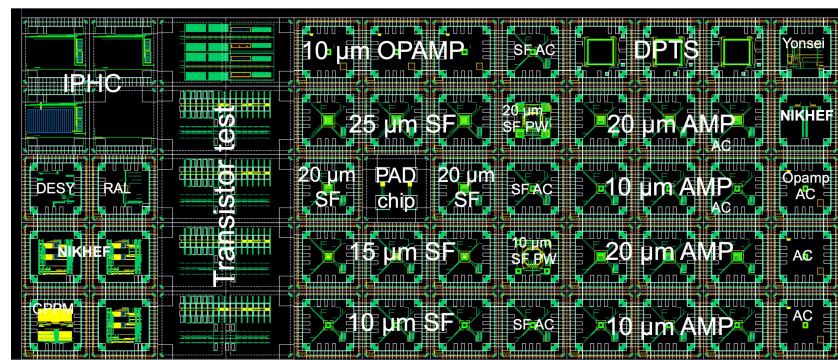


Silicon bridge between 2 MALTA chips



- MALTA 3 will merge latest process modifications, and front-end design with improved time resolution and asynchronous read-out
- Main features: nanosecond time resolution, full reticle size, data streaming, chainable sensor, integration into LPGBT read-out
- Focus on radiation hardness and high granularity
- Ongoing digital design flow, MPW submission expected by Q1 2022

- Dedicated chips and test structures on MLR1
 - IPHC: rolling shutter larger matrices
 - DESY: Krummenacher feedback
 - RAL: LVDS/CML receiver/driver
 - NIKHEF: bandgap, T-sensor, VC
 - CPPM: ring-oscillators
 - Yonsei: amplifier structures
- GDS submitted Dec 1, 2020. Wafers delivered first half of June.
 - First chips delivered on blue tape in August, first samples distributed and being mounted on test cards
- Working on the next submission with two stitched chips and some other.

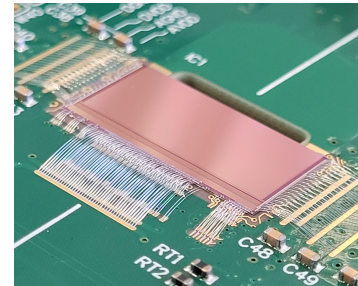
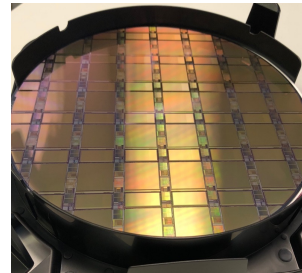
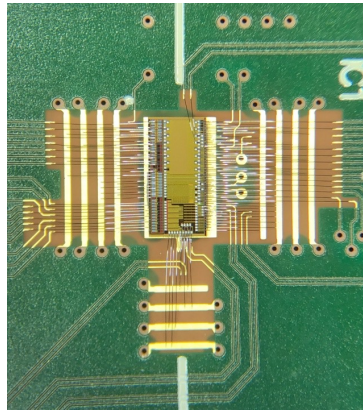
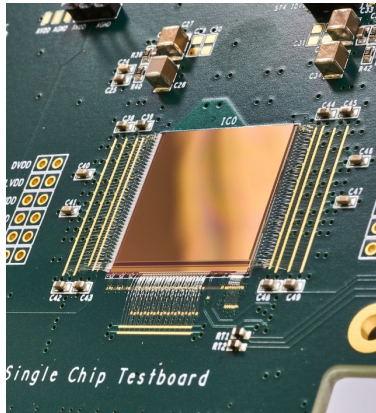


- MALTA sensors produced in TowerJazz 180 nm CMOS technology with small collection electrode are an interesting candidate for future experiments
- 36.4 μm^2 pixel pitch with low power asynchronous read-out make them attractive for high granularity detectors
- Additional process modifications (gap in n- layer and extra deep p-well) showed full efficiency after 10^{15} n/cm² neutron irradiation
- Substrate engineering (Czochralski substrates) show increase tracking and timing resolution due to increased depletion depth and charge sharing

- This project has received funding from the European Union's Horizon 2020 Research and Innovation programme under grant agreement No 101004761.
- Supported by the Marie Skłodowska-Curie Innovative Training Network of the European Commission Horizon 2020 Programme under contract number 675587 (STREAM).
- The measurements leading to these results have been performed at the TestBeam Facility at DESY Hamburg (Germany), a member of the Helmholtz Association (HGF).
- Measurements leading to these results have been performed at the E3 beam-line at the electron accelerator ELSA operated by the university of Bonn in Nordrhein-Westfalen, Germany.
- This project has received funding from the European Union's Horizon 2020 Research and Innovation programme under Grant Agreement no. 654168.(IJS, Ljubljana, Slovenia)
- Dr. Ben Phoenix, Prof. David Parker and the operators at the MC40 cyclotron in Birmingham (UK).

STREAM

AIDA Innova WP5 and
CERN EP R&D WP 1.2



MALTA3
#digital-flow-design

MALTA1 & MLVL

Mini-MALTA

MALTA C

MALTA 2

MALTA 3

Jan 2018

Jan 2019

Aug 2019

Jan 2021

2023

Large demonstrator
Asynchronous readout
Electrode size and reset
mechanism evaluation

Small demonstrator
Process and mask
modification

Slow control
improvements on EPI
and Czochralski
substrates

New front-end
Additional process
modification

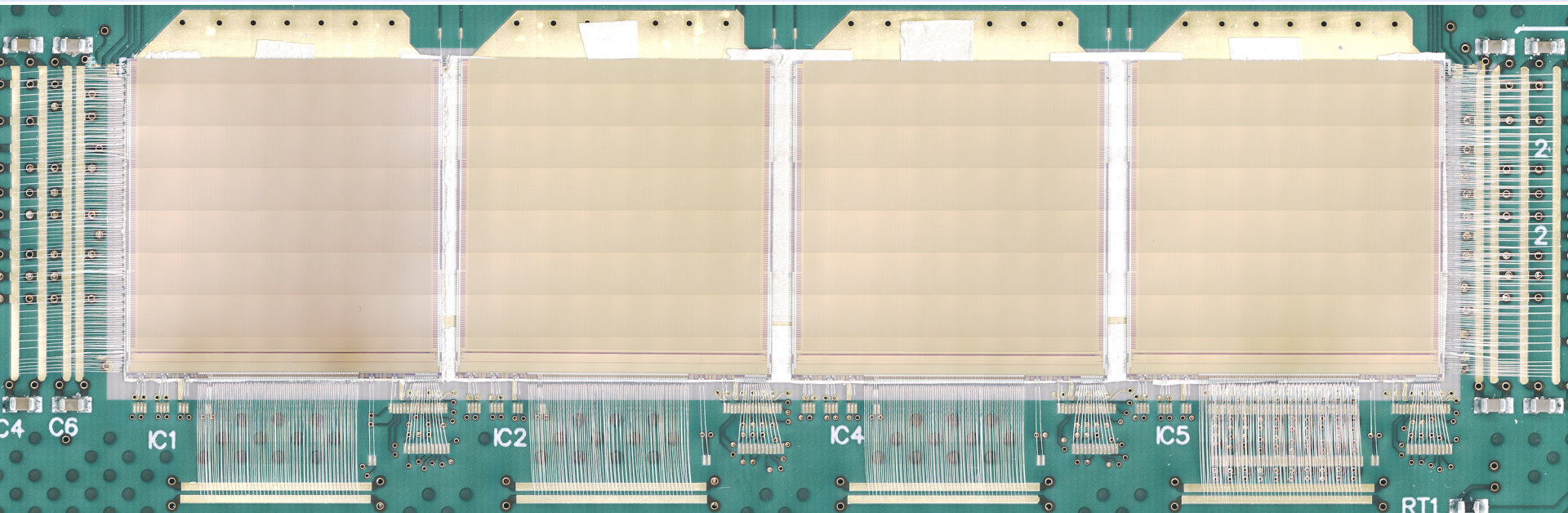
Large matrix
Time tagging

Poor lateral field after
irradiation

Full efficiency after
 $1e15 \text{ n/cm}^2$
Enlarged cluster size and
improved time resolution
on Czochralski

Improved time resolution
and on chip synchronization

Bonus

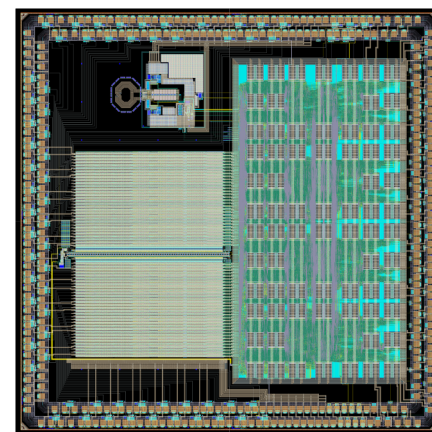


MALTA 4 chip module

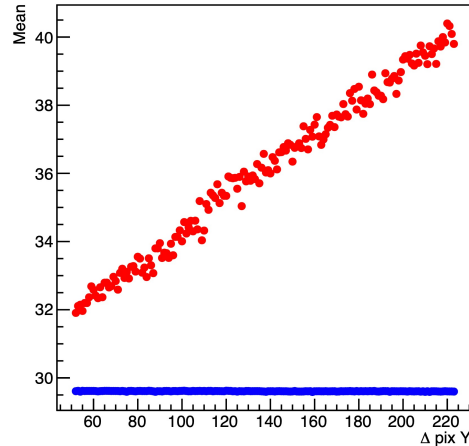
- Module with 4 MALTA sensors
- Daisy chain data into single output
- Use a rad-hard ASIC for read-out and control
 - Testing today with pico-TDC
 - Plan to use LPGBT in the future



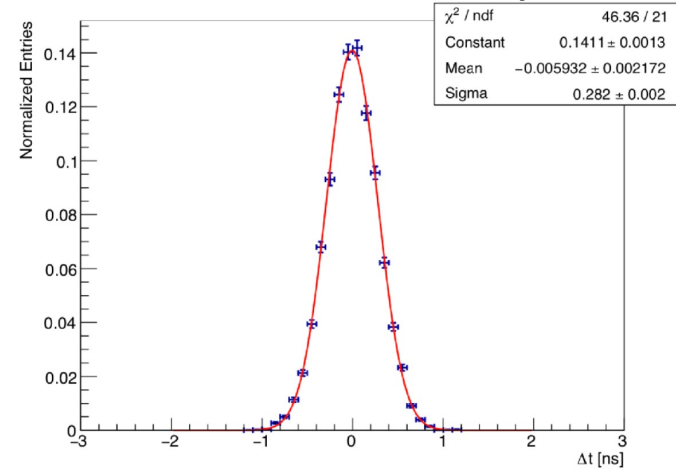
LPGBTX



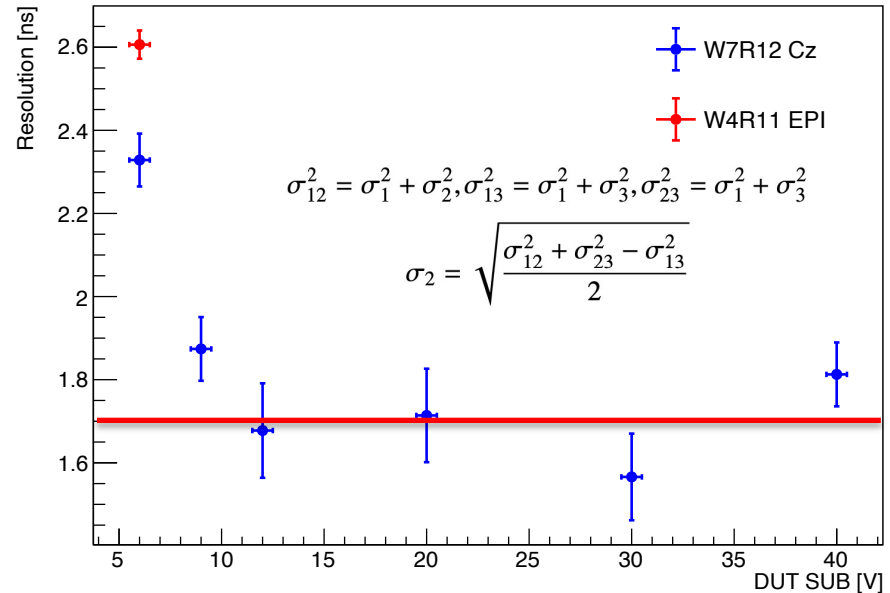
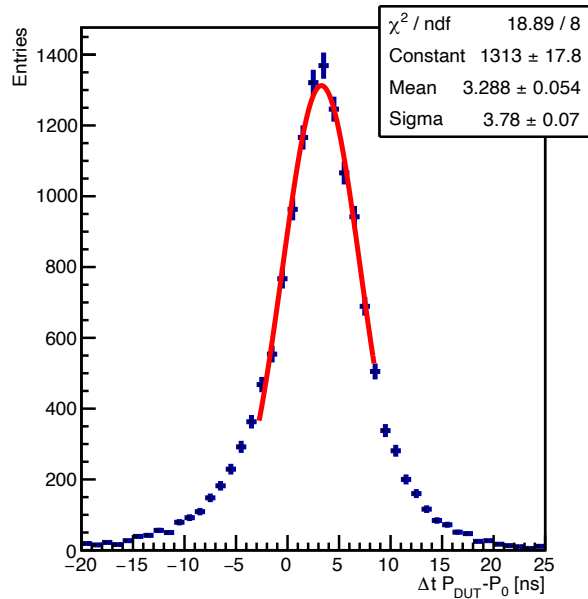
Pico-TDC



MALTA2 Cz XDPW 100 μm thick

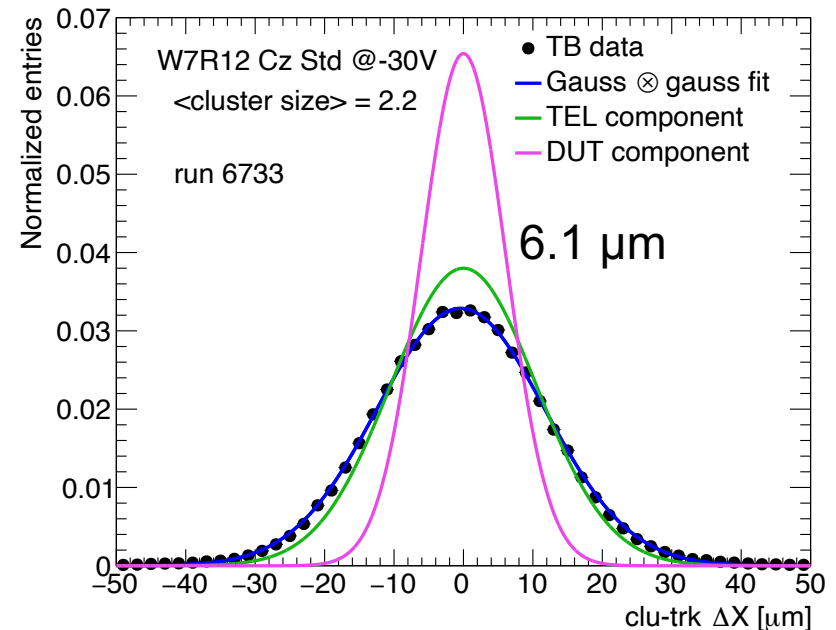
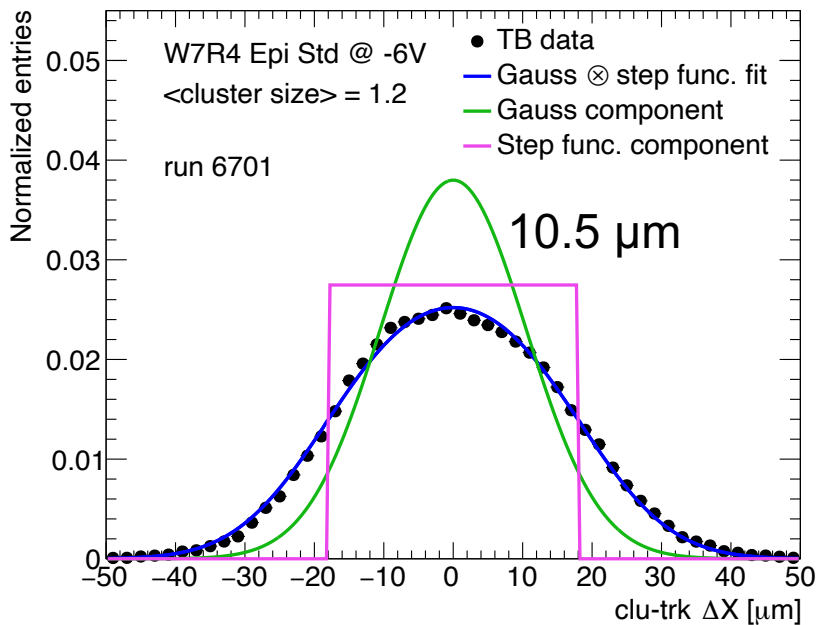


- Jitter of the MALTA2 front-end electronics measured every 5th column on Cz XDPW sensors thinned down to 100 μm for two different doping concentrations. Higher doping has 372 ± 2.2 ps jitter while the low doping has 282 ± 2 ps jitter. Timing is obtained by injecting charge to two-pixel on a column at the same time. Time distribution of injections are measured with PicoTDC and the measurement is repeated for all pixels on the columns.



- Resolution is extracted from the linear combination of the time differences of reference MALTA signals between planes from test-beam data
- Measurement of lead time of cluster using Pico-TDC *
- Time resolution on EPI sample is 2.60 ± 0.05 ns at 6 V, while the time resolution on the Czochralski sample is compatible with 1.7 ± 0.1 ns between 10 V and 30 V.

- Using General Broken Lines (GBL) algorithm for track reconstruction to mitigate multiple scattering effects (few GeV electron beam)
 - Embedded in Proteus software [M. Kiehn et al., 0.5281/zenodo.2586736]
- Extracted telescope resolution is $10.5 \mu\text{m}$ from the convolution of a gaussian distribution with a two-sided step distribution with $36.4 \mu\text{m}$ width corresponding to the pixel pitch of MALTA
- Can improve tracking resolution of telescope up to $6.1 \mu\text{m}$ by using Czochralski samples at higher bias (30V) for reference planes (increased charge sharing)



MALTA 4-chip carrier board

